

Title (en)  
LOW-CAPACITY VERTICAL DIODE

Title (de)  
VERTIKALE DIODE MIT SCHWACHER KAPAZITÄT

Title (fr)  
DIODE VERTICALE DE FAIBLE CAPACITE

Publication  
**EP 1428264 A1 20040616 (FR)**

Application  
**EP 02783155 A 20020910**

Priority  
• FR 0203080 W 20020910  
• FR 0111680 A 20010910

Abstract (en)  
[origin: FR2829616A1] A vertical diode with front face mounting and of low capacity in a semiconductor substrate (1) comprises: (a) a projecting first zone incorporating at least one semiconducting layer (3) doped with a conductivity type opposite to that of the substrate, the upper surface of the semiconducting layer carrying a first solder bead (23); and (b) a second zone incorporating on the substrate a thin conducting track (16) carrying at least two second solder beads (24). The first and second solder beads define a plane parallel to the plane of the substrate. An Independent claim is also included for the formation of a vertical diode with front face mounting and low capacity in a semiconductor substrate.

IPC 1-7  
**H01L 29/861**; **H01L 29/868**

IPC 8 full level  
**H01L 29/861** (2006.01); **H01L 29/868** (2006.01)

CPC (source: EP US)  
**H01L 29/8613** (2013.01 - EP US); **H01L 29/868** (2013.01 - EP US); **Y02E 10/548** (2013.01 - EP)

Citation (search report)  
See references of WO 03026020A1

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